

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

International Application No.: PCT/DE2004/001838

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By: Chen et al.

For: Vertical Nano-Transistor, Method of Its
Fabrication and Memory Arrangement

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9 February 2006

Hon.
Commissioner for Patents
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Mail Stop PCT**Preliminary Amendment Prior To Claims Fee Calculation**

Sir:

With a view to placing the English translation of their instant International Application into a condition believed to conform to American patent prosecution standards, Applicants courteously request entry of the following amendment:

In the Specification:

Page 1, line 7: cancel "Specification" and substitute
-BACKGROUND OF THE INVENTION.

1. Field of the Invention.- therefor;

line 11: insert -2. The Prior Art.-;

Page 2, line 2: insert -OBJECT OF THE INVENTION.-;

line 8: insert -SUMMARY OF THE INVENTION.-;

Page 4, lines 15 and 16: cancel and substitute therefor
-DESCRIPTION OF THE DRAWINGS.

The novel features which are considered to be characteristic of the invention are set forth with particularity in the appended claims. The invention